Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	S08
Core Size	8-Bit
Speed	40MHz
Connectivity	I²C, SCI, SPI
Peripherals	LCD, LVD, PWM
Number of I/O	53
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.9K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08lg32clh

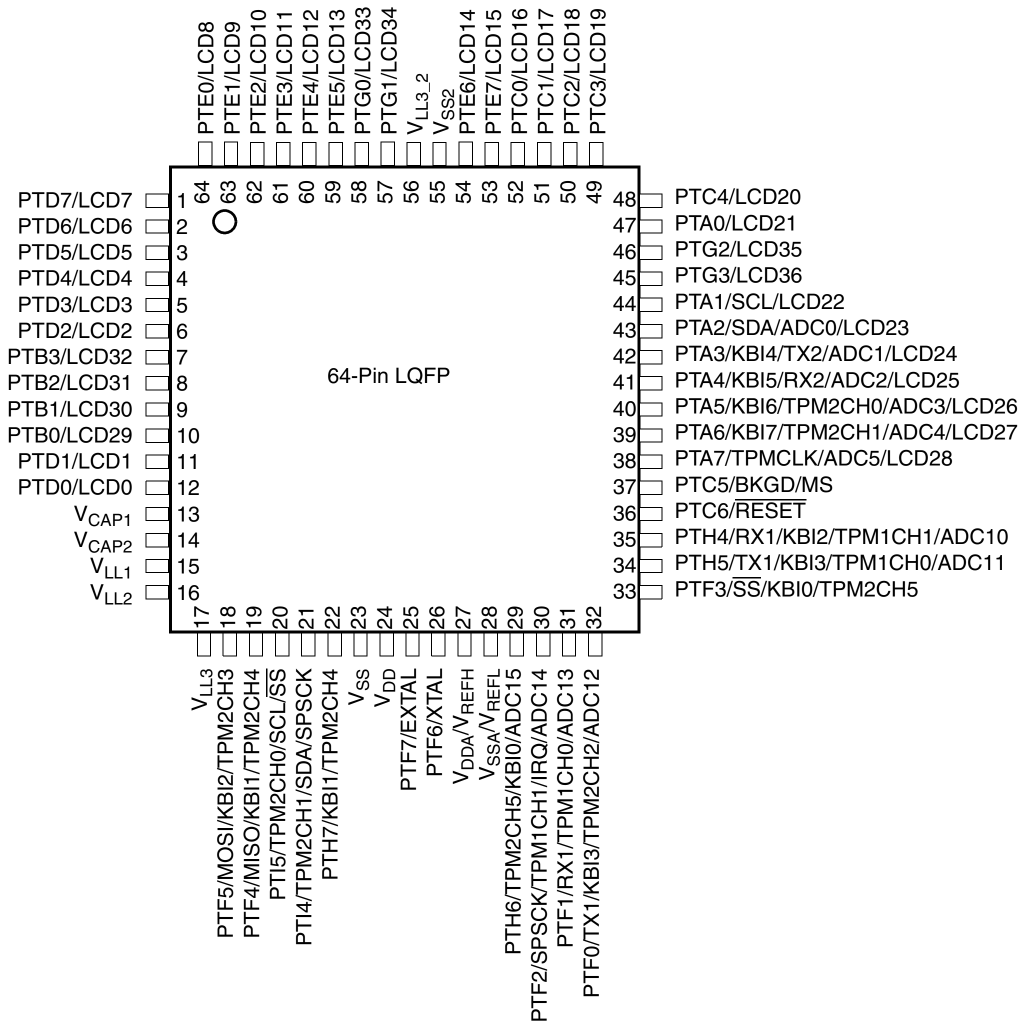


Figure 3. 64-Pin LQFP

NOTE

V_{REFH}/V_{REFL} are internally connected to V_{DDA}/V_{SSA}.

Table 2. Pin Availability by Package Pin-Count

Packages			<-- Lowest **Priority** --> Highest				
80	**64**	**48**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
1	1	1	PTD7	LCD7	—	—	—
2	2	2	PTD6	LCD6	—	—	—
3	3	3	PTD5	LCD5	—	—	—
4	4	4	PTD4	LCD4	—	—	—
5	5	5	PTD3	LCD3	—	—	—
6	6	6	PTD2	LCD2	—	—	—
7	7	—	PTB3	LCD32	—	—	—
8	8	—	PTB2	LCD31	—	—	—
9	—	—	PTB7	LCD40	—	—	—
10	—	—	PTB6	LCD39	—	—	—
11	—	—	PTB5	LCD38	—	—	—
12	—	—	PTB4	LCD37	—	—	—
13	9	—	PTB1	LCD30	—	—	—
14	10	—	PTB0	LCD29	—	—	—
15	11	7	PTD1	LCD1	—	—	—
16	12	8	PTD0	LCD0	—	—	—
17	13	9	V_{CAP1}	—	—	—	—
18	14	10	V_{CAP2}	—	—	—	—
19	15	11	V_{LL1}	—	—	—	—
20	16	12	V_{LL2}	—	—	—	—
21	17	13	V_{LL3}	—	—	—	—
22	18	14	PTF5	MOSI	KBI2	TPM2CH3	—
23	19	15	PTF4	MISO	KBI1	TPM2CH4	—
24	20	—	PTI5	TPM2CH0	SCL	$\overline{SS}$	—
25	21	—	PTI4	TPM2CH1	SDA	SPSCK	—
26	—	—	PTI3	TPM2CH2	MOSI	—	—
27	—	—	PTI2	TPM2CH3	MISO	—	—
28	—	—	PTI1	TMRCLK	TX2	—	—
29	—	—	PTI0	RX2	—	—	—
30	22	—	PTH7	KBI1	TPM2CH4	—	—
31	23	16	V_{SS}	—	—	—	—
32	24	17	V_{DD}	—	—	—	—
33	25	18	PTF7	EXTAL	—	—	—
34	26	19	PTF6	XTAL	—	—	—
35	27	20	V_{DDA}	V_{REFH}	—	—	—
36	28	21	V_{SSA}	V_{REFL}	—	—	—
37	29	—	PTH6	TPM2CH5	KBI0	ADC15	—
38	30	22	PTF2	SPSCK	TPM1CH1	IRQ	ADC14

Table 4. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to +5.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25 ±2	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages and use the largest of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in an external power supply going out of regulation. Ensure that the external V_{DD} load will shunt current greater than maximum injection current, this will be of greater risk when the MCU is not consuming power. For instance, if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

2.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in On-Chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 5. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H –40 to +105	°C
Maximum junction temperature	T_J	125	°C
Thermal resistance Single-layer board 80-pin LQFP 64-pin LQFP 48-pin LQFP	θ_{JA}	61 71 80	°C/W
Thermal resistance Four-layer board 80-pin LQFP 64-pin LQFP 48-pin LQFP	θ_{JA}	48 52 56	°C/W

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \textit{Eqn. 1}$$

Table 7. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	2500	—	V
2	Charge device model (CDM)	V_{CDM}	750	—	V
3	Latch-up current at T_A = 85 °C	I_{LAT}	±100	—	mA

[1] Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

2.6 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 8. DC Characteristics

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1	—	Operating Voltage	—	2.7	—	5.5	V
2	P	Output high voltage — Low Drive (PTxDSn = 0) 5 V, I_{Load} = –2 mA 3 V, I_{Load} = –0.6 mA	V_{OH}	 V_{DD} – 0.8 V_{DD} – 0.8	 — —	 — —	V
		Output high voltage — High Drive (PTxDSn = 1) V 5 V, I_{Load} = –10 mA 3 V, I_{Load} = –3 mA		 V_{DD} – 0.8 V_{DD} – 0.8	 — —	 — —	
3	P	Output low voltage — Low Drive (PTxDSn = 0) 5 V, I_{Load} = 2 mA 3 V, I_{Load} = 0.6 mA	V_{OL}	—	 — —	 0.8 0.8	V
		Output low voltage — High Drive (PTxDSn = 1) 5 V, I_{Load} = 10 mA 3 V, I_{Load} = 3 mA			 — —	 0.8 0.8	
4	P	Output high current — Max total I_{OH} for all ports 5 V 3 V	I_{OHT}	—	—	 100 60	mA
5	C	Output high current — Max total I_{OL} for all ports 5 V 3 V	I_{OLT}	—	—	 100 60	mA
6	P	Bandgap voltage reference	V_{BG}	—	1.225	—	V
7	P	Input high voltage; all digital inputs	V_{IH}	0.65 x V_{DD}	—	—	V
8	P	Input low voltage; all digital inputs	V_{IL}	—	—	0.35 x V_{DD}	V
9	P	Input hysteresis; all digital inputs	V_{hys}	0.06 x V_{DD}	—	—	mV
10	P	Input leakage current; input only pins[2] $V_{In} = V_{DD}$ or V_{SS}	$\lvert I_{In} \rvert$	—	0.1	1	µA
11	P	High impedence (off-state) leakage current $V_{In} = V_{DD}$ or V_{SS}	$\lvert I_{OZ} \rvert$	—	0.1	1	µA
12	P	Internal pullup resistors[3]	R_{PU}	20	45	65	kΩ
13	P	Internal pulldown resistors[4]	R_{PD}	20	45	65	kΩ

2.7 Supply Current Characteristics

This section includes information about power supply current in various operating modes.

Table 9. Supply Current Characteristics

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
1	C	Run supply current FEI mode, all modules on	RI_{DD}	20 MHz	3	16.38	27.85	mA	–40 °C to 85 °C
	C						28.05		–40 °C to105 °C
	C			1 MHz		1.67	2.84		–40 °C to 85 °C
	C						2.87		–40 °C to105 °C
	P			20 MHz	5	16.55	28.14	mA	–40 °C to 85 °C
	P						28.35		–40 °C to105 °C
	C			1 MHz		1.77	3.01		–40 °C to 85 °C
	C						3.05		–40 °C to105 °C
2	T	Run supply current FEI mode, all modules off	RI_{DD}	20 MHz	3	11.9	20.25	mA	–40 °C to 85 °C
	T						21.72		–40 °C to105 °C
	T			1 MHz		1.16	1.95		–40 °C to 85 °C
	T						1.98		–40 °C to105 °C
	T			20 MHz	5	12.68	21.56	mA	–40 °C to 85 °C
	T						23.12		–40 °C to105 °C
	T			1 MHz		1.4	2.39		–40 °C to 85 °C
	T						2.41		–40 °C to105 °C
3	T	Wait mode supply current FEI mode, all modules off	WI_{DD}	20 MHz	3	7.9	13.42	mA	–40 °C to 85 °C
	T						13.59		–40 °C to105 °C
	T			1 MHz		0.88	1.49		–40 °C to 85 °C
	T						1.51		–40 °C to105 °C
	P			20 MHz	5	8.13	13.81	mA	–40 °C to 85 °C
	P						13.98		–40 °C to105 °C
	T			1 MHz		1.12	1.91		–40 °C to 85 °C
	T						1.94		–40 °C to105 °C
4	C	Stop2 mode supply current	$S2I_{DD}$	n/a	3	1.1	16.0	µA	–40 °C to 85 °C
	C						39.0		–40 °C to105 °C
	P				5	1.2	18.7	µA	–40 °C to 85 °C
	P						46.1		–40 °C to105 °C
5	C	Stop3 mode supply current No clocks active	$S3I_{DD}$	n/a	3	1.2	22.4	µA	–40 °C to 85 °C
	C						56.2		–40 °C to105 °C
	P				5	1.32	25.5	µA	–40 °C to 85 °C
	P						63.9		–40 °C to105 °C

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter		Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
6	T	Stop2 adders:	RTC using LPO	—	n/a	3	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.25	—	µA	
			LCD[2] with rbias (Low Gain)				1.2[3]	—		
			LCD[2] with rbias (High Gain)				18[4]	—		
			LCD[2] with Cpump				4.05[3]	—		–40 °C to 85 °C
			RTC using LPO			5	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.22	—	µA	
			LCD[2] with rbias (Low Gain)				1.5[3]	—		
			LCD[2] with rbias (High Gain)				32[4]	—		
			LCD[2] with Cpump				7.12[3]	—		–40 °C to 85 °C
7	T	Stop3 adders:	RTC using LPO	—	n/a	3	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.75	—	µA	
			LCD[2] with rbias (Low Gain)				1.2[3]	—		
			LCD[2] with rbias (High Gain)				18[4]	—		
			LCD[2] with Cpump				4.35[3]	—		–40 °C to 85 °C
			RTC using LPO			5	230	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.74	—	µA	
			LCD[2] with rbias (Low Gain)				1.5[3]	—		
			LCD[2] with rbias (High Gain)				32[4]	—		
			LCD[2] with Cpump				7.49[3]	—		–40 °C to 85 °C

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter		Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
8	T	Stop3 adders:	EREFSTEN = 1	—	n/a	3	4.58	—	µA	–40 °C to 105 °C
			IREFSTEN = 1				71.7	—		
			LVD				94.35	—		
			EREFSTEN = 1			5	4.61	—	µA	
			IREFSTEN = 1				71.69	—		
			LVD				107.34	—		

1 Typical values are measured at 25 °C. Characterized, not tested.
2 LCD configured for Charge Pump Enabled V_{LL3} connected to V_{DD}.
3 This does not include current required for 32 kHz oscillator.
4 This is the maximum current when all LCD inputs/outputs are used.

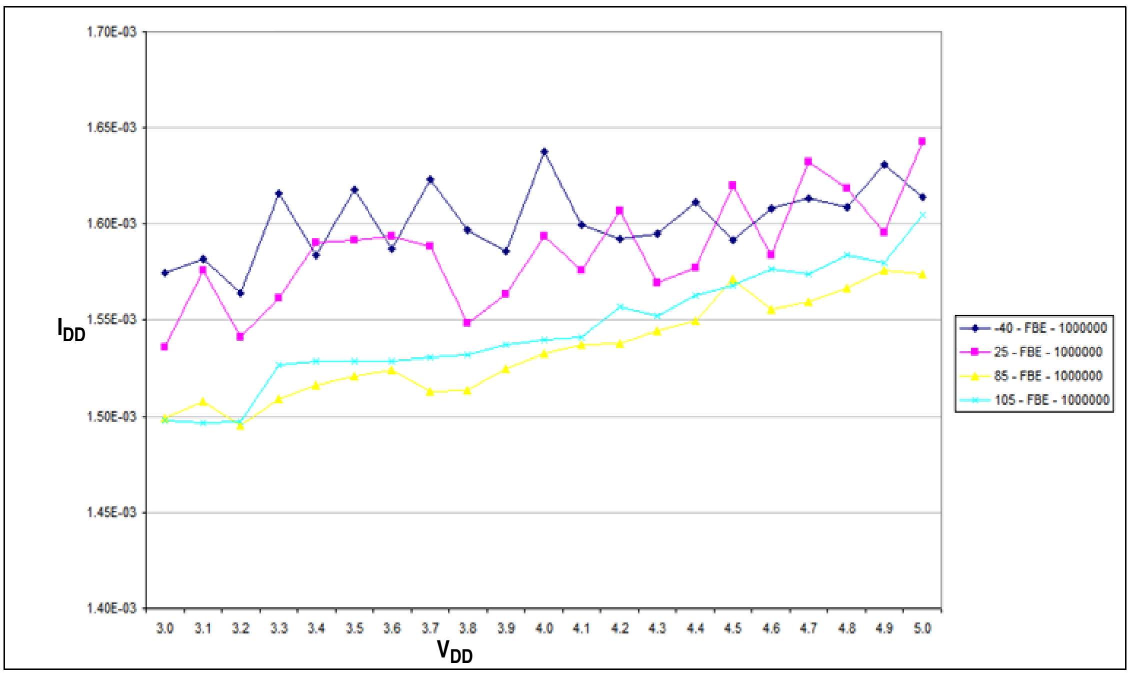


Figure 9. Typical Run I_{DD} for FBE Mode at 1 MHz

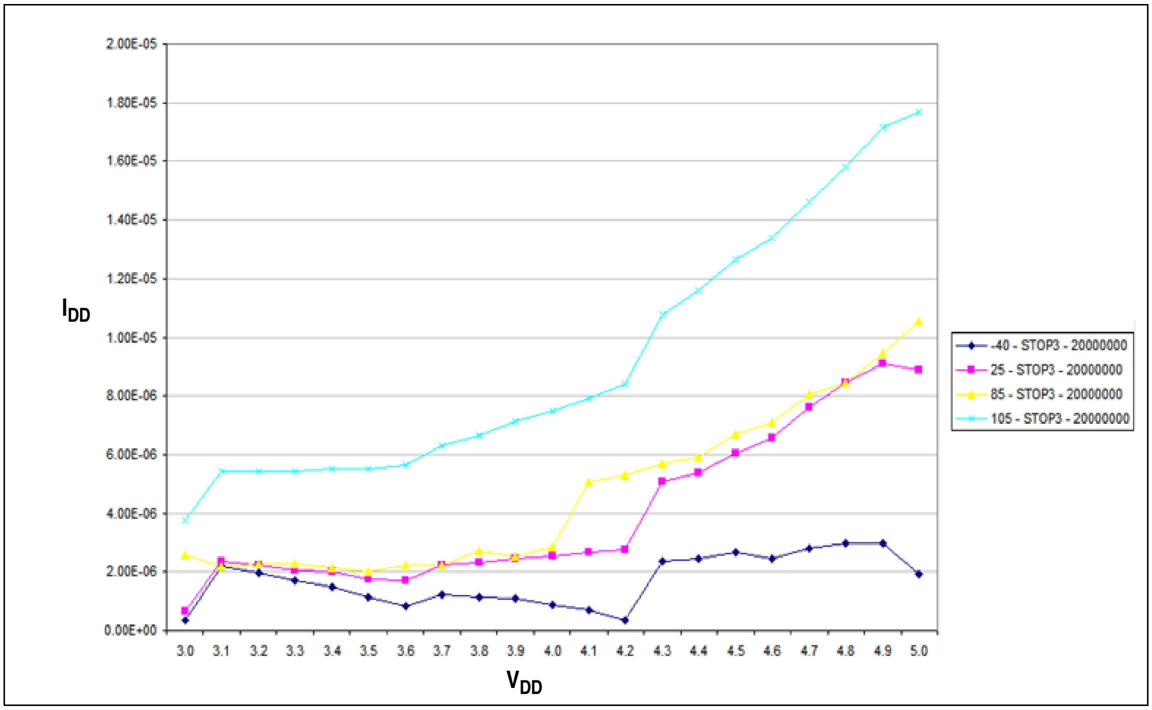


Figure 14. Typical Stop3 I_{DD}

2.8 External Oscillator (XOSC) Characteristics

Table 10. Oscillator Electrical Specifications (Temperature Range = –40 °C to 105 °C Ambient)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1	D	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) • Low range (RANGE = 0) • High range (RANGE = 1) FEE or FBE mode[2] • High range (RANGE = 1, HGO = 1) BLPE mode • High range (RANGE = 1, HGO = 0) BLPE mode	 f_{lo} f_{hi} $f_{hi\text{-}hgo}$ $f_{hi\text{-}lp}$	 32 1 1 1	 — — — —	 38.4 5 16 8	 kHz MHz MHz MHz
2	D	Load capacitors	C_1 C_2	See crystal or resonator manufacturer’s recommendation.			

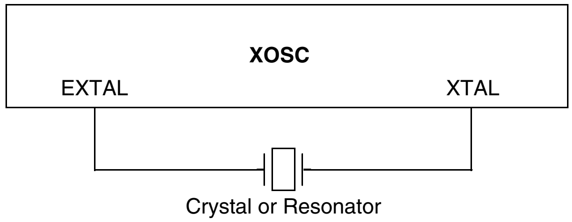


Figure 16. Typical Crystal or Resonator Circuit: Low Range/Low Power

2.9 Internal Clock Source (ICS) Characteristics

Table 11. ICS Frequency Specifications (Temperature Range = –40 °C to 105 °C Ambient)

Num	C	Characteristic		Symbol	Min	Typ[1]	Max	Unit
1	P	Average internal reference frequency — factory trimmed at VDD = 5.0 V and temperature = 25 °C		f_{int_ft}	—	32.768	—	kHz
2	C	Average internal reference frequency — user trimmed		f_{int_t}	31.25	—	39.0625	kHz
3	C	Internal reference start-up time		t_{IRST}	—	60	100	µs
4	P	DCO output frequency range — trimmed[2]	Low range (DRS = 00)	f_{dco_t}	16	—	20	MHz
	P		Mid range (DRS = 01)		32	—	40	
5	P	DCO output frequency[2] Reference = 32768 Hz and DMX32 = 1	Low range (DRS = 00)	f_{dco_DMX32}	—	19.92	—	MHz
	P		Mid range (DRS = 01)		—	39.85	—	
6	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)[3]		$\Delta f_{dco\_res\_t}$	—	±0.1	±0.2	$\%f_{dco}$
7	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)[3]		$\Delta f_{dco\_res\_t}$	—	±0.2	±0.4	$\%f_{dco}$
8	P	Total deviation of trimmed DCO output frequency over voltage and temperature		Δf_{dco_t}	—	–1.0 to +0.5	±2	$\%f_{dco}$
9	C	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0 °C to 70 °C[3]		Δf_{dco_t}	—	±0.5	±1	$\%f_{dco}$
10	C	FLL acquisition time[3, 4]		$t_{Acquire}$	—	—	1	mS
11	C	Long term jitter of DCO output clock (averaged over 2 ms interval)[5]		C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This parameter is characterized and not tested on each device.

4 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

5 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in the crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

Table 13. 12-bit ADC Characteristics ($V_{REFH} = V_{DDAD}$, $V_{REFL} = V_{SSAD}$)

Num	C	Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
1	T	Supply Current ADLPC = 1 ADLSMP = 1 ADCO = 1	—	I_{DDAD}	—	195	—	µA	—
2	T	Supply Current ADLPC = 1 ADLSMP = 0 ADCO = 1	—	I_{DDAD}	—	347	—	µA	—
3	T	Supply Current ADLPC = 0 ADLSMP = 1 ADCO = 1	—	I_{DDAD}	—	407	—	µA	—
4	P	Supply Current ADLPC = 0 ADLSMP = 0 ADCO = 1	—	I_{DDAD}	—	0.755	1	mA	—
5	—	Supply Current	Stop, Reset, Module Off	IDDAD		0.011	1	µA	—
6	P	ADC Asynchronous Clock Source	High Speed (ADLPC=0)	f_{ADACK}	2	3.3	5	MHz	$t_{ADACK} = 1/f_{ADACK}$
			Low Power (ADLPC=1)		1.25	2	3.3		
7	C	Conversion Time (Including sample time)	Short sample (ADLSMP=0)	t_{ADC}	—	20	—	ADCK cycles	See *ADC chapter in the LG32 Reference Manual* for conversion time variances
			Long sample (ADLSMP=1)		—	40	—		
8	C	Sample Time	Short sample (ADLSMP=0)	t_{ADS}	—	3.5	—	ADCK cycles	
			Long sample (ADLSMP=1)		—	23.5	—		
9	T	Total Unadjusted Error	12-bit mode	E_{TUE}	—	±3.0	—	LSB[2]	Includes quantization
	P		10-bit mode		—	±1	±2.5		
	T		8-bit mode		—	±0.5	±1		
10	T	Differential Non-Linearity	12-bit mode	DNL	—	±1.75	—	LSB[2]	
	P		10-bit mode[3]		—	±0.5	±1.0		
	T		8-bit mode[3]		—	±0.3	±0.5		
11	T	Integral Non-Linearity	12-bit mode	INL	—	±1.5	—	LSB[2]	
	P		10-bit mode		—	±0.5	±1		
	T		8-bit mode		—	±0.3	±0.5		
12	T	Zero-Scale Error	12-bit mode	E_{ZS}	—	±1.5	—	LSB[2]	$V_{ADIN} = V_{SSAD}$
	P		10-bit mode		—	±0.5	±1.5		
	T		8-bit mode		—	±0.5	±0.5		

Table 13. 12-bit ADC Characteristics ($V_{REFH} = V_{DDAD}$, $V_{REFL} = V_{SSAD}$) (continued)

Num	C	Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
13	T	Full-Scale Error	12-bit mode	E_{FS}	—	±1	—	LSB[2]	$V_{ADIN} = V_{DDAD}$
	P		10-bit mode		—	±0.5	±1		
	T		8-bit mode		—	±0.5	±0.5		
14	D	Quantization Error	12-bit mode	E_Q	—	–1 to 0	—	LSB[2]	—
			10-bit mode		—	—	±0.5		
			8-bit mode		—	—	±0.5		
15	D	Input Leakage Error	12-bit mode	E_{IL}	—	±1	—	LSB[2]	Pad leakage[4] * R_{AS}
			10-bit mode		—	±0.2	±2.5		
			8-bit mode		—	±0.1	±1		
16	C	Temp Sensor Slope	–40 °C to 25 °C	m	—	1.646	—	mV/°C	—
			25 °C to 125°C		—	1.769	—		
17	C	Temp Sensor Voltage	25 °C	V_{TEMP25}	—	701.2	—	mV	—

[1] Typical values assume V_{DDAD} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

[2] 1 LSB = $(V_{REFH} – V_{REFL})/2^N$

[3] Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes

[4] Based on input pad leakage current. Refer to pad electricals.

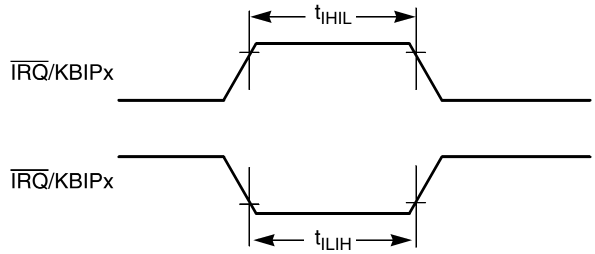


Figure 20. $\overline{IRQ}$/KBIPx Timing

2.11.2 TPM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 15. TPM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

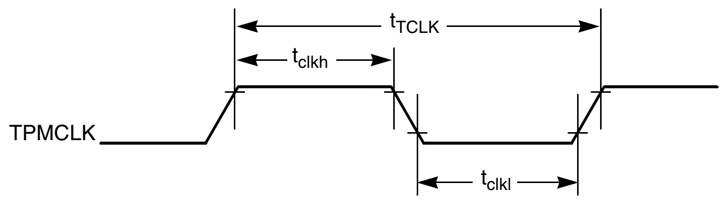


Figure 21. Timer External Clock

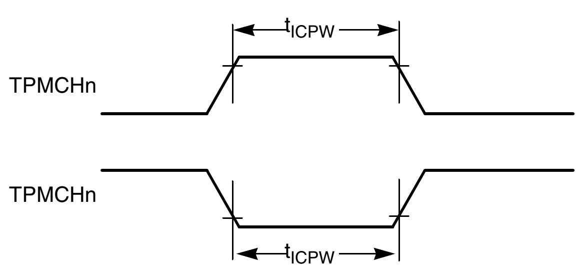
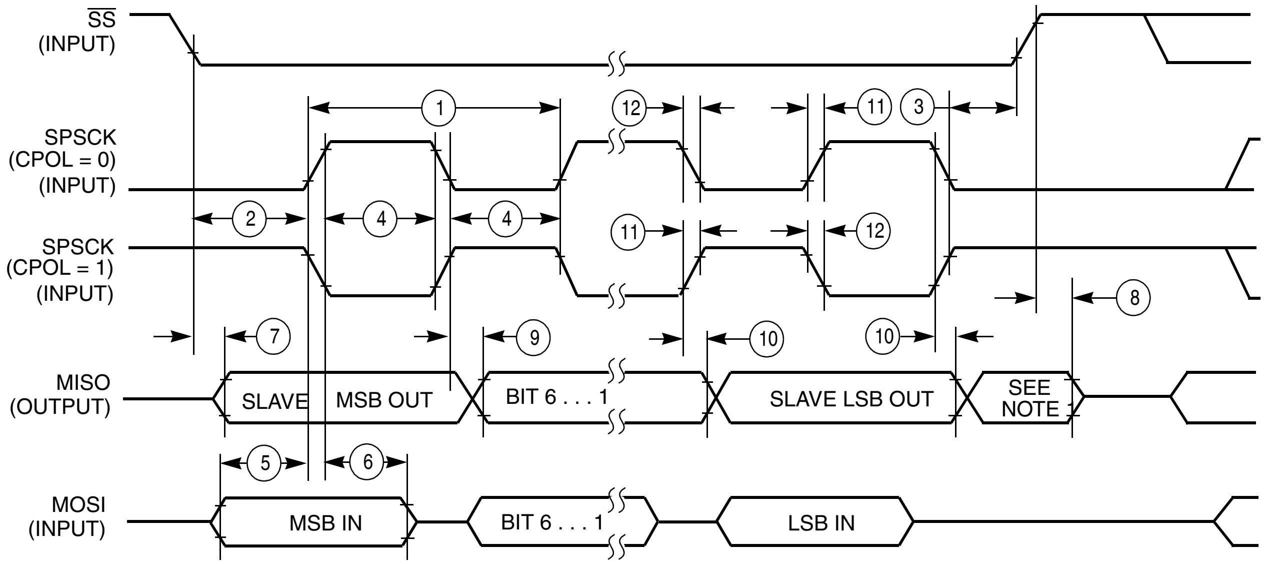


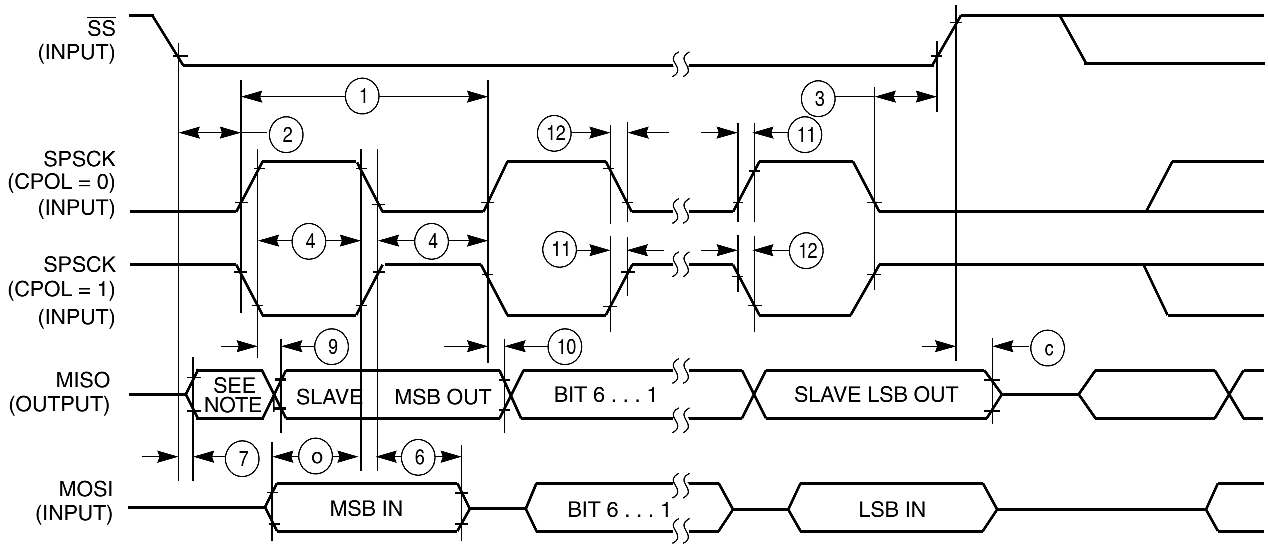
Figure 22. Timer Input Capture Pulse



NOTE:

1. Not defined but normally MSB of character just received.

Figure 25. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 26. SPI Slave Timing (CPHA = 1)

2.12 LCD Specifications

Table 17. LCD Electricals, 3 V Glass

C	Characteristic	Symbol	Min	Typ	Max	Units
D	VLL3 Supply Voltage	VLL3	2.7	—	5.5	V
D	LCD Frame Frequency	f_{Frame}	28	30	64	Hz
D	LCD Charge Pump Capacitance	C_{LCD}	—	100	100	pF
D	LCD Bypass Capacitance	C_{BYLCD}	—	100	100	
D	LCD Glass Capacitance	C_{glass}	—	2000	8000	

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

Table 18. Flash Characteristics

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage for program/erase –40 °C to 85 °C	$V_{prog/erase}$	2.7		5.5	V
D	Supply voltage for read operation	V_{Read}	2.7		5.5	V
D	Internal FCLK frequency[1]	f_{FCLK}	150		200	kHz
D	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	μs
C	Byte program time (random location)[2]	t_{prog}		9		t_{Fcyc}
C	Byte program time (burst mode)[2]	t_{Burst}		4		t_{Fcyc}
C	Page erase time[2]	t_{Page}		4000		t_{Fcyc}
C	Mass erase time[2]	t_{Mass}		20,000		t_{Fcyc}
D	Byte program current[3]	R_{IDDBP}	—	4	—	mA
D	Page erase current[3]	R_{IDDPE}	—	6	—	mA
C	Program/erase endurance[4] T_L to T_H = –40 °C to + 85 °C T = 25 °C		10,000	— 100,000	— —	cycles
C	Data retention[5]	t_{D_ret}	15	100	—	years

1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 The program and erase currents are additional to the standard run I_{DD}. These values are measured at room temperatures with V_{DD} = 5.0 V, bus frequency = 4.0 MHz.

4 **Typical endurance for flash** was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to *Engineering Bulletin EB619, Typical Endurance for Nonvolatile Memory.*

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25 °C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to *Engineering Bulletin EB618, Typical Data Retention for Nonvolatile Memory.*

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East).

The maximum radiated RF emissions of the tested configuration in all orientations are less than or equal to the reported emissions levels.

Table 19. Radiated Emissions, Electric Field

Parameter	Symbol	Conditions	Frequency	f_{OSC}/f_{BUS}	Level[1] (Max)	Unit
Radiated emissions, electric field	V_{RE_TEM}	V_{DD} = 5.5 T_A = +25 °C Package type = 80 LQFP	0.15 – 50 MHz	4 MHz crystal 16 MHz bus	10	dBμV
			50 – 150 MHz		14	
			150 – 500 MHz		8	
			500 – 1000 MHz		5	
			IEC Level		L	—
			SAE Level		2	—

1 Data based on qualification test results.

2.14.2 Conducted Transient Susceptibility

Microcontroller transient conducted susceptibility is measured in accordance with an internal Freescale test method. The measurement is performed with the microcontroller installed on a custom EMC evaluation board and running specialized EMC test software designed in compliance with the test method. The conducted susceptibility is determined by injecting the transient susceptibility signal on each pin of the microcontroller. The transient waveform and injection methodology is based on IEC 61000-4-4 (EFT/B). The transient voltage required to cause performance degradation on any pin in the tested configuration is greater than or equal to the reported levels unless otherwise indicated by footnotes below Table 20.

Table 20. Conducted Susceptibility, EFT/B

Parameter	Symbol	Conditions	f_{OSC}/f_{BUS}	Result	Amplitude[1] (Min)	Unit
Conducted susceptibility, electrical fast transient/burst (EFT/B)	V_{CS_EFT}	V_{DD} = 5.5 T_A = +25 °C Package type = 80-pin LQFP	4 kHz crystal 4 MHz bus	A B C D	>4.0[2] >4.0[3] >4.0[4] >4.0	kV

1 Data based on qualification test results. Not tested in production.

2 Exceptions as covered in footnotes 3 and 4.

3 Except pins PHT1, PTH2, PTH3, PTH4, PTH5. See figures below for values.

4 Except pins PTF3, PTH5, PTH4, PHT0, Reset, and BKGD. See figures below for values.

Individual performance of each pin is shown in Figure 27, Figure 28, Figure 29, and Figure 30.

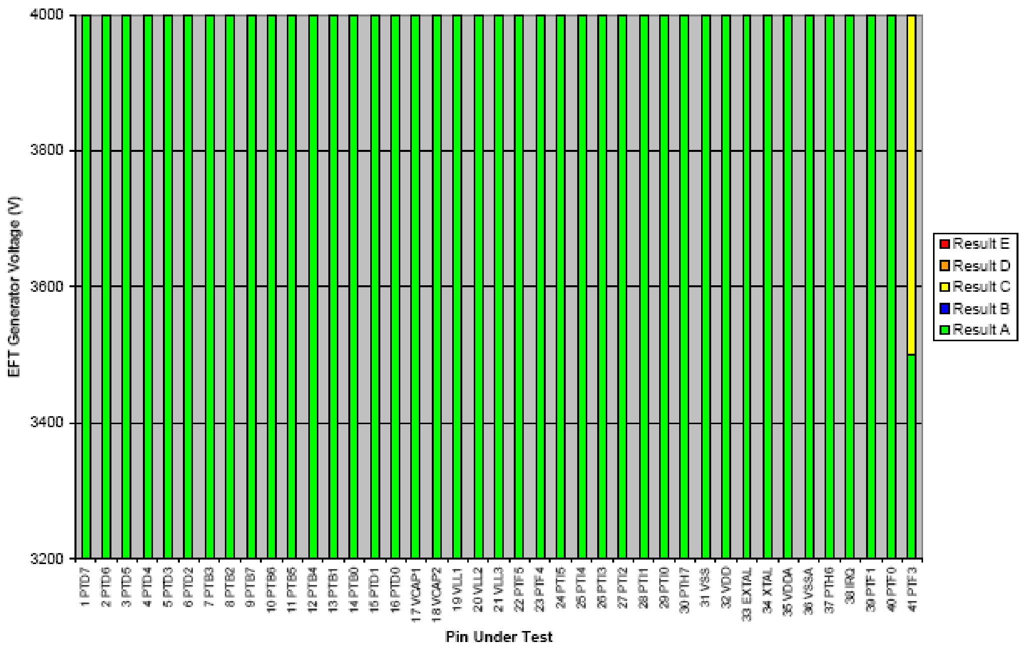
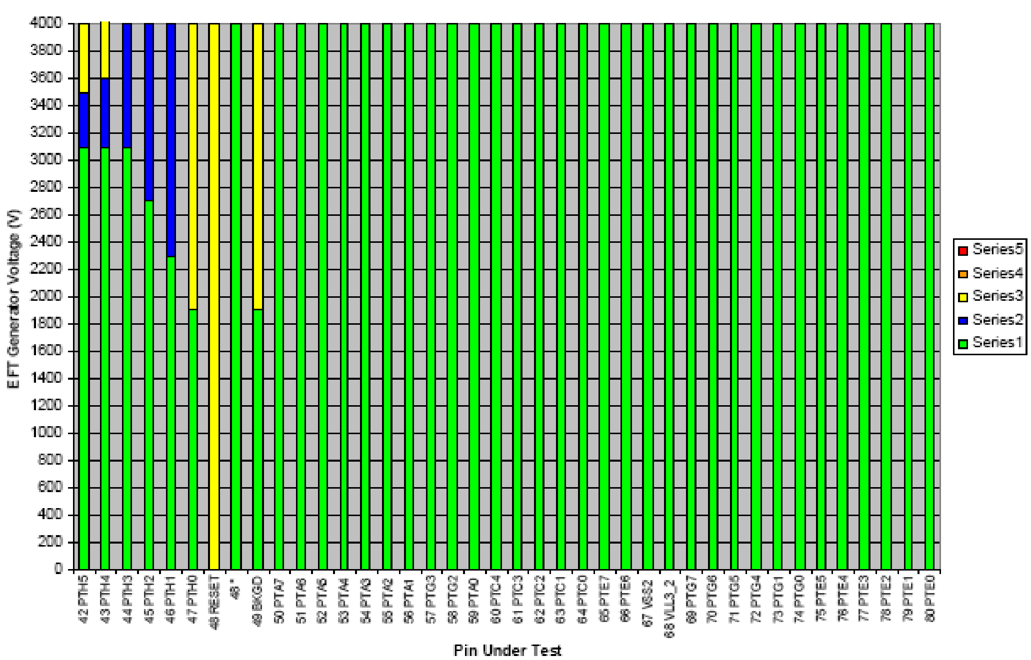


Figure 27. 4 MHz, Positive Polarity Pins 1 – 41



Note:
RESET retested with 0.1 μF capacitor from pin to ground is Class A compliant as shown by 48*.

Figure 28. 4 MHz, Positive Polarity Pins 42 – 80

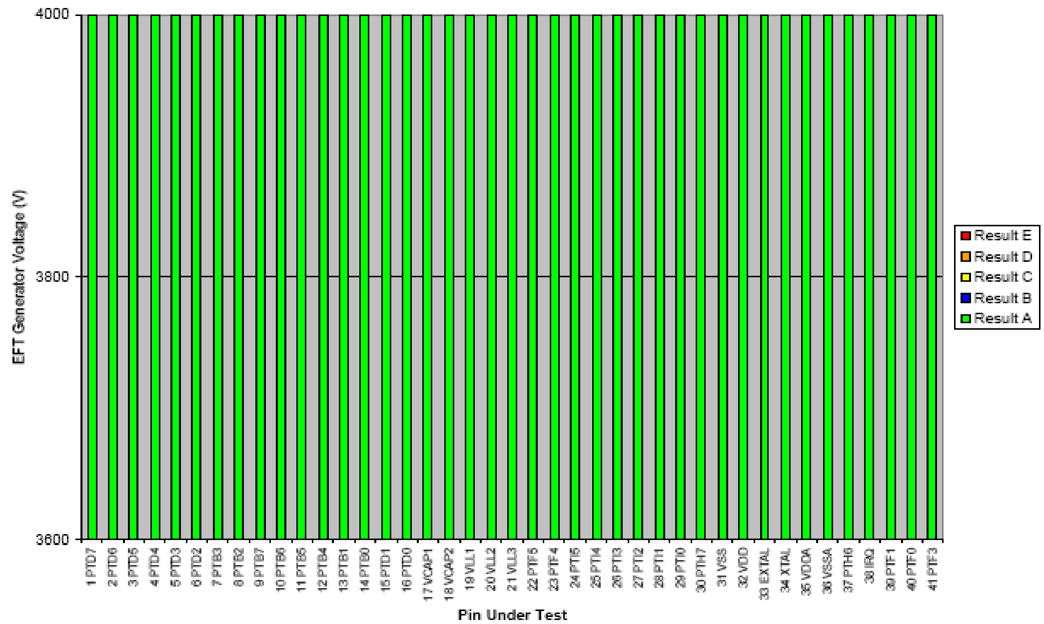
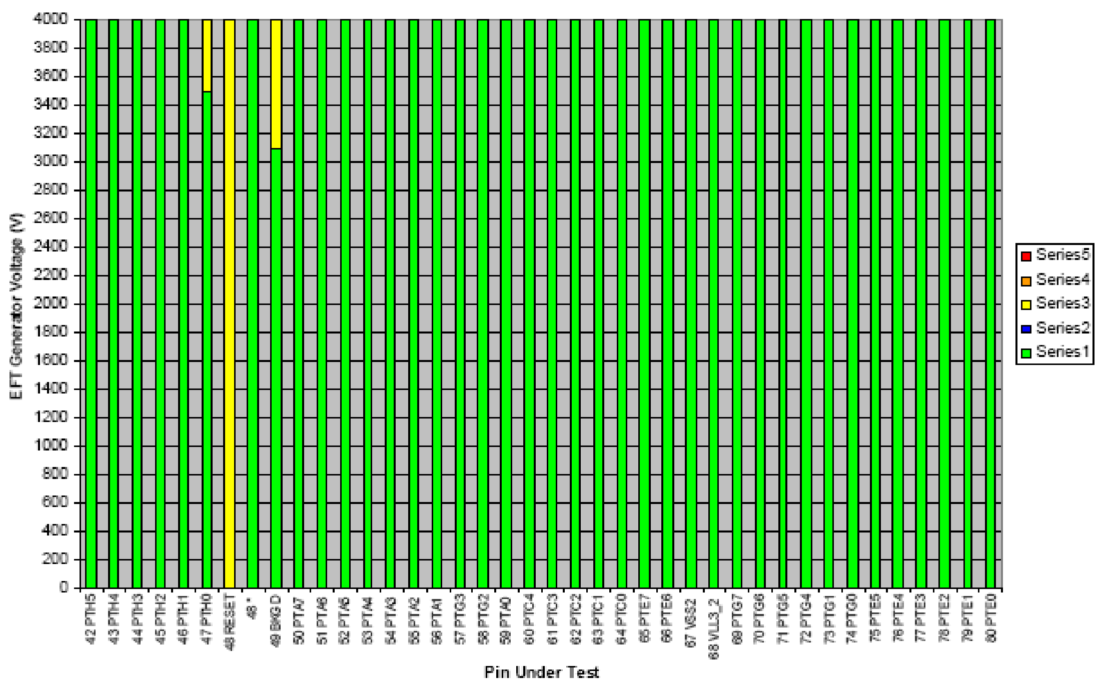


Figure 29. 4 MHz, Negative Polarity Pins 1 – 41



Note:
RESET retested with 0.1 µF capacitor from pin to ground is Class A compliant as shown by 48*.

Figure 30. 4 MHz, Negative Polarity Pins 42 – 80

The susceptibility performance classification is described in Table 21.

Table 21. Susceptibility Performance Classification

Result	Performance Criteria	
A	No failure	The MCU performs as designed during and after exposure.
B	Self-recovering failure	The MCU does not perform as designed during exposure. The MCU returns automatically to normal operation after exposure is removed.
C	Soft failure	The MCU does not perform as designed during exposure. The MCU does not return to normal operation until exposure is removed and the RESET pin is asserted.
D	Hard failure	The MCU does not perform as designed during exposure. The MCU does not return to normal operation until exposure is removed and the power to the MCU is cycled.
E	Damage	The MCU does not perform as designed during and after exposure. The MCU cannot be returned to proper operation due to physical damage or other permanent performance degradation.

3 Ordering Information

This section contains ordering information for MC9S08LG32 and MC9S08LG16 devices.

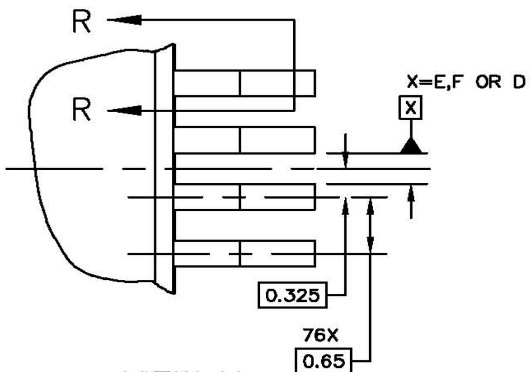
Table 22. Device Numbering System

Device Number[1]	Memory		Temperature Range (°C)	LCD Mode Operation	Available Packages[2]
	FLASH	RAM			
Auto					
S9S08LG32J0CLK	32 KB	1984	-40 °C to +85 °C	Charge Pump	80-pin LQFP
S9S08LG32J0CLH					64-pin LQFP
S9S08LG32J0CLF					48-pin LQFP
S9S08LG32J0VLK	32 KB	1984	-40 °C to +105 °C	Register Bias	80-pin LQFP
S9S08LG32J0VLH					64-pin LQFP
S9S08LG32J0VLF					48-pin LQFP
S9S08LG16J0VLH	18 KB	1984			64-pin LQFP
S9S08LG16J0VLF					48-pin LQFP
IMM					
MC9S08LG32CLK	32 KB	1984	-40 °C to + 85 °C	Charge Pump	80-pin LQFP
MC9S08LG32CLH					64-pin LQFP
MC9S08LG32CLF					48-pin LQFP
MC9S08LG16CLH	18 KB	1984			64-pin LQFP
MC9S08LG16CLF					48-pin LQFP

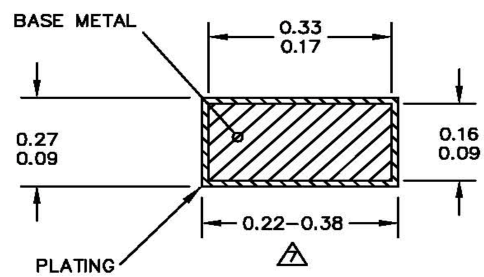
1 See the *MC9S08LG32 Reference Manual* (document MC9S08LG32RM), for a complete description of modules included on each device.

2 See Table 23 for package information.

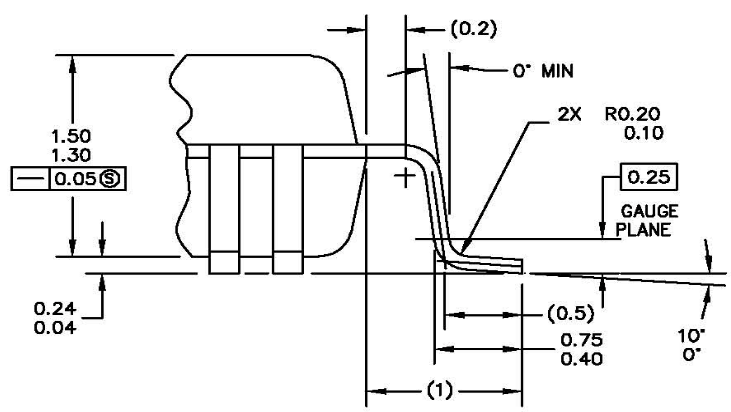
freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23237W
		PAGE: 917A
© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED. ELECTRONIC VERSIONS ARE UNCONTROLLED EXCEPT WHEN ACCESSED DIRECTLY FROM THE DOCUMENT CONTROL REPOSITORY. PRINTED VERSIONS ARE UNCONTROLLED EXCEPT WHEN STAMPED "CONTROLLED COPY" IN RED.	DO NOT SCALE THIS DRAWING	REV: E



VIEW Y



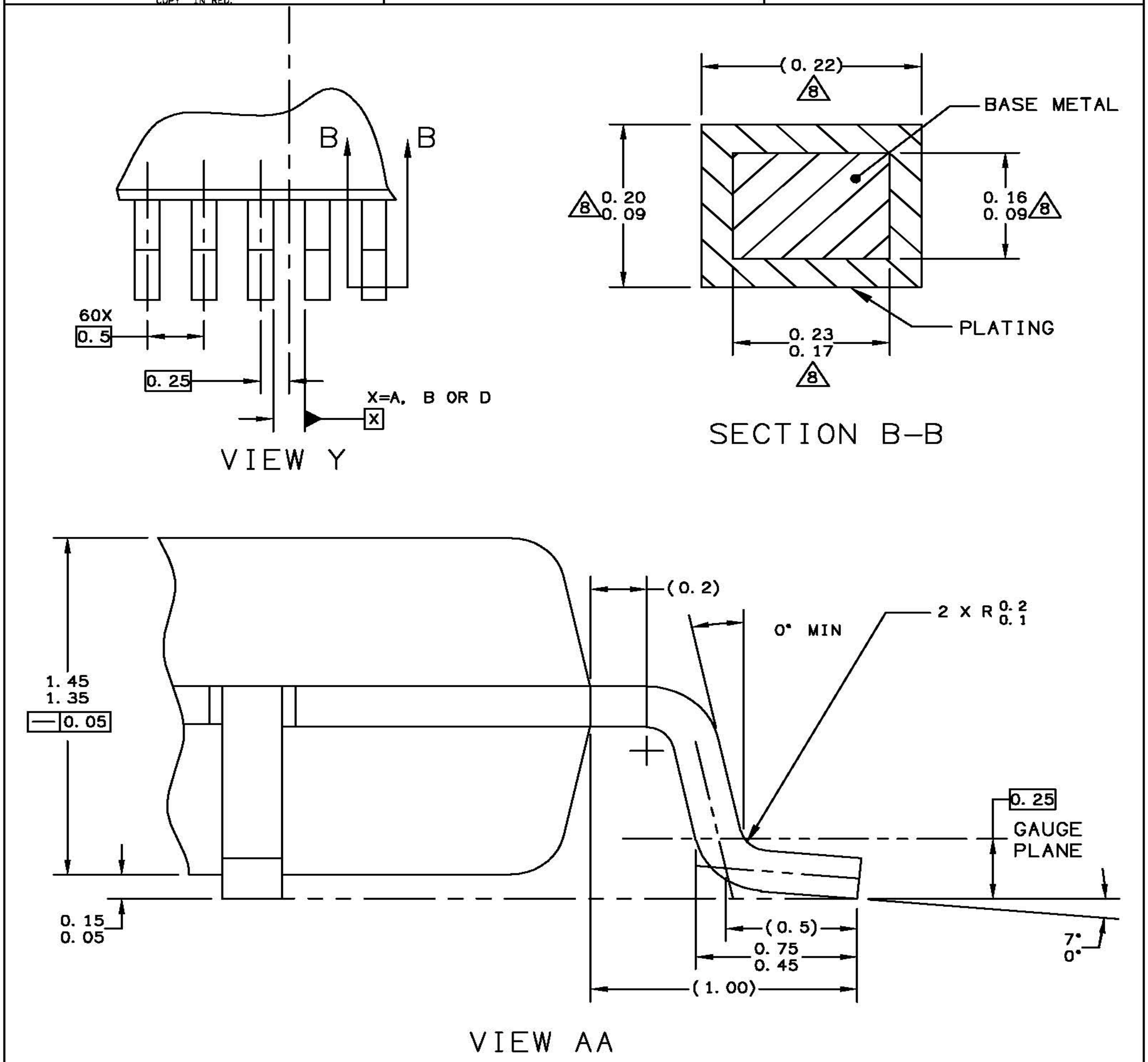
SECTION R–R
ROTATED 90° CW



VIEW K

TITLE: 80 LD LQFP, 14 X 14 PKG, 0.65 MM PITCH, 1.4 THICK	CASE NUMBER: 917A–03	
	STANDARD: FREESCALE	
	PACKAGE CODE: 8258	SHEET: 2 OF 3

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
		PAGE: 840F
	DO NOT SCALE THIS DRAWING	REV: E



TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 2 OF 3